

Description

- High speed switching application.
- Analog switch application.

Features

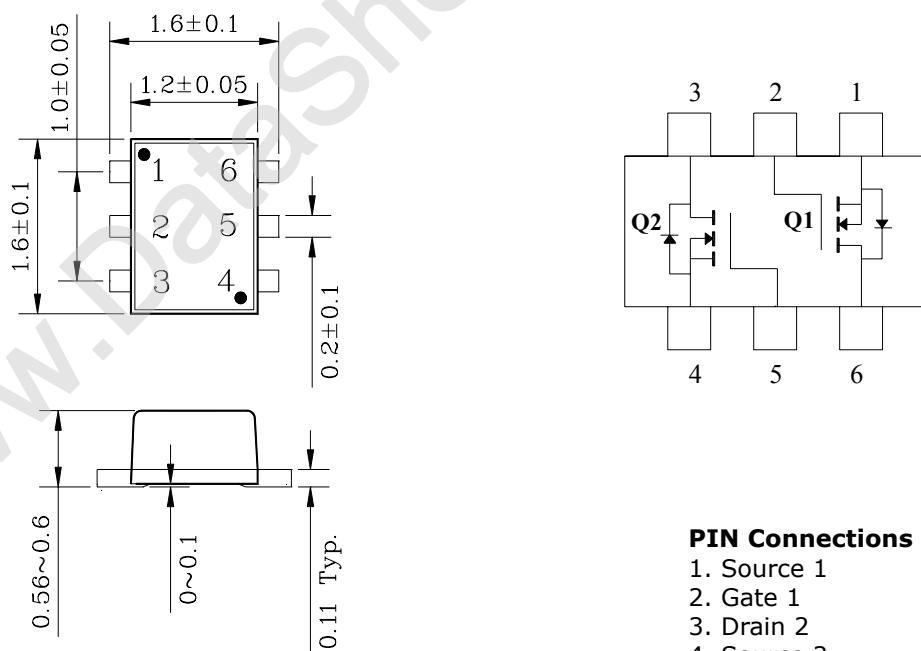
- 2.5V Gate drive.
- Low threshold voltage : $V_{th} = 0.5 \sim 1.5V$.
- Two STK1828 Chips in SOT-563F Package.

Ordering Information

Type NO.	Marking	Package Code
SUF621EF	H	SOT-563F

Outline Dimensions

unit : mm

**PIN Connections**

1. Source 1
2. Gate 1
3. Drain 2
4. Source 2
5. Gate 2
6. Drain1

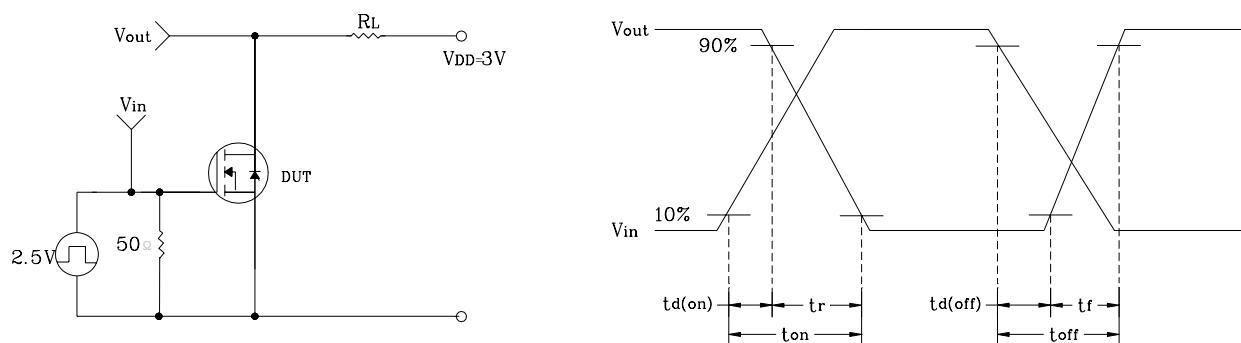
Absolute maximum ratings (Q1,Q2 Common) (Ta=25°C)

Characteristic	Symbol	Ratings	Unit
Drain-Source voltage	V _{DS}	20	V
Gate-Source voltage	V _{GSS}	10	V
DC Drain current	I _D	50	mA
Drain Power dissipation	P _D	100	mW
Channel temperature	T _{ch}	150	°C
Storage temperature range	T _{stg}	-55~150	°C

Electrical Characteristics (Q1,Q2 Common) (Ta=25°C)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Drain-Source breakdown voltage	BV _{DSS}	I _D =100μA, V _{GS} =0	20			V
Gate-Threshold voltage	V _{th}	I _D =0.1mA, V _{DS} =3V	0.5		1.5	V
Drain cut-off current	I _{DSS}	V _{DS} =20V, V _{GS} =0			1	μA
Gate leakage current	I _{GSS}	V _{GS} =10V, V _{DS} =0			1	μA
Drain-Source on-resistance	R _{DS(ON)}	V _{GS} =2.5V, I _D =10mA		20	40	Ω
Forward transfer admittance	Y _{fs}	V _{DS} =3V, I _D =10mA	20			mS
Input capacitance	C _{iss}	V _{DS} =3V, V _{GS} =0, f=1MHz		5.5		pF
Output capacitance	C _{oss}	V _{DS} =3V, V _{GS} =0, f=1MHz		6.5		pF
Reverse Transfer capacitance	C _{rss}	V _{DS} =3V, V _{GS} =0, f=1MHz		1.6		pF
Turn-on time	t _{on}	V _{DD} =3V, I _D =10mA V _{GEN} =0~2.5V		0.14		μs
Turn-off time	t _{off}	V _{DD} =3V, I _D =10mA V _{GEN} =0~2.5V		0.14		μs

* Switching Time Test Circuit



Electrical Characteristic Curves

Fig.1 ID - VDS

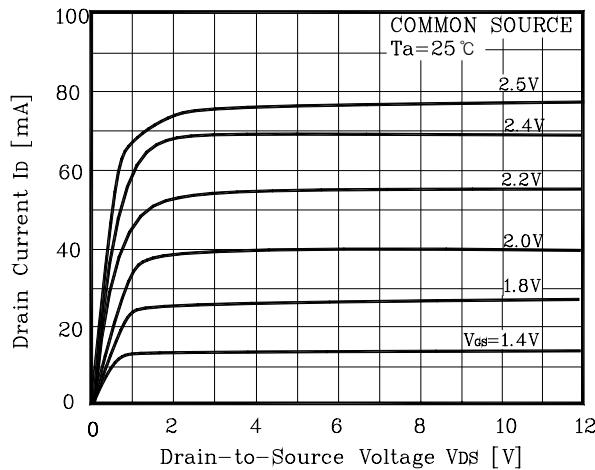


Fig.2 PD - Ta

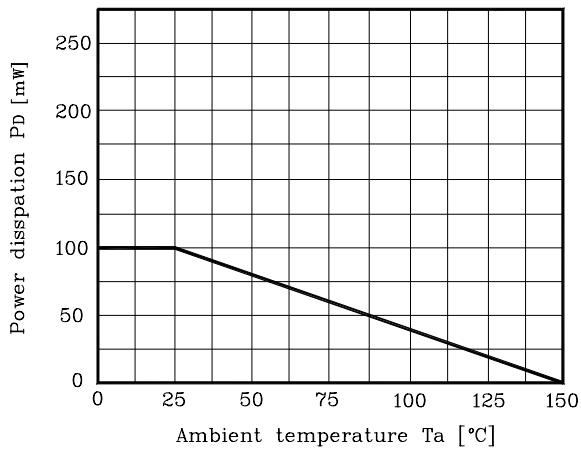


Fig.3 IDR - VDS

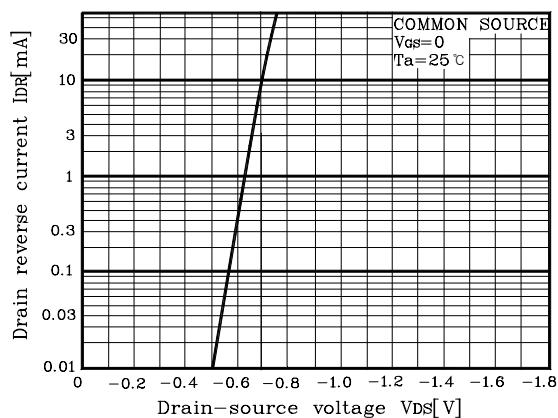


Fig.4 ID - VGS

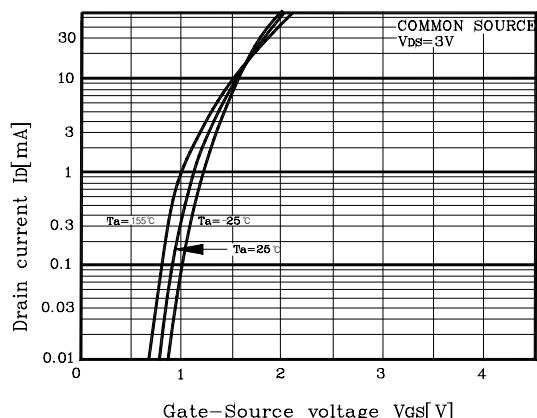


Fig.5 | Yfs | - ID

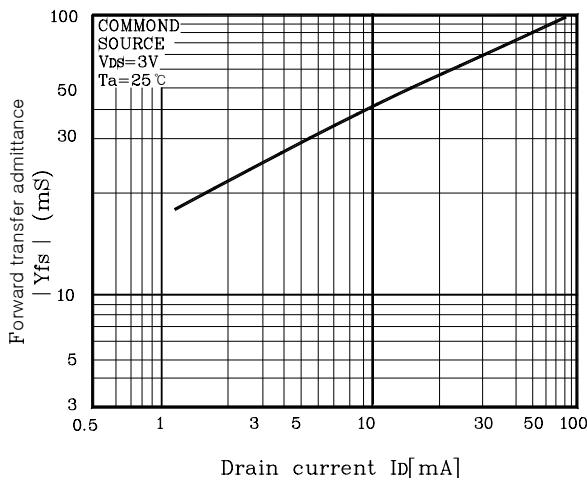
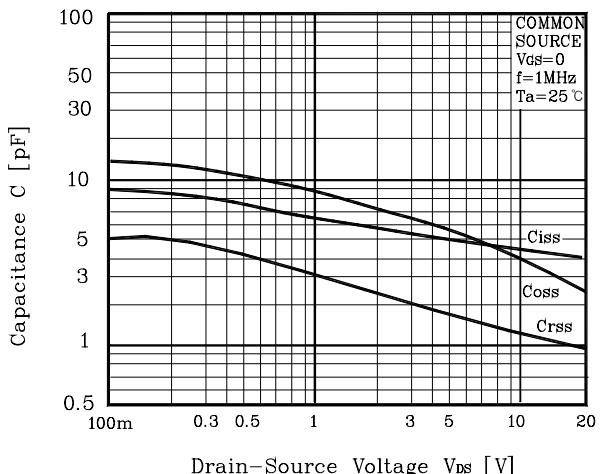


Fig.6 C - VDS



Electrical Characteristic Curves

Fig.7 V_{DS} - I_D

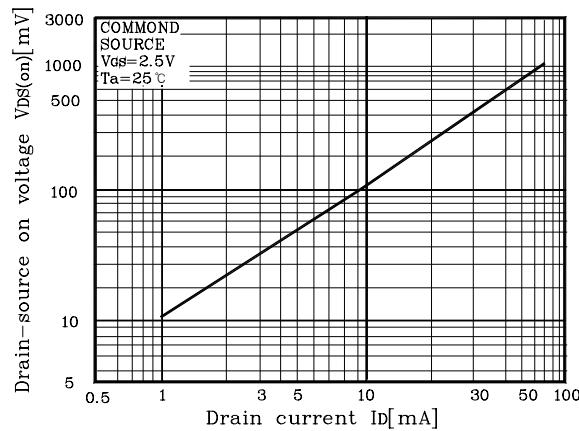


Fig.8 t - I_D

